阅读申明

- 1.本站收集的数据手册和产品资料都来自互联网,版权归原作者所有。如读者和版权方有任何异议请及时告之,我们将妥善解决。
- 2.本站提供的中文数据手册是英文数据手册的中文翻译,其目的是协助用户阅读,该译文无法自动跟随原稿更新,同时也可能存在翻译上的不当。建议读者以英文原稿为参考以便获得更精准的信息。
- 3.本站提供的产品资料,来自厂商的技术支持或者使用者的心得体会等,其内容可能存在描 叙上的差异,建议读者做出适当判断。
- 4.如需与我们联系,请发邮件到marketing@iczoom.com,主题请标有"数据手册"字样。

Read Statement

- 1. The datasheets and other product information on the site are all from network reference or other public materials, and the copyright belongs to the original author and original published source. If readers and copyright owners have any objections, please contact us and we will deal with it in a timely manner.
- 2. The Chinese datasheets provided on the website is a Chinese translation of the English datasheets. Its purpose is for reader's learning exchange only and do not involve commercial purposes. The translation cannot be automatically updated with the original manuscript, and there may also be improper translations. Readers are advised to use the English manuscript as a reference for more accurate information.
- 3. All product information provided on the website refer to solutions from manufacturers' technical support or users the contents may have differences in description, and readers are advised to take the original article as the standard.
- 4. If you have any questions, please contact us at marketing@iczoom.com and mark the subject with "Datasheets" .

ICE 1QS01

Controller for Quasiresonant Switch Mode Power Supplies Supporting Low Power Standby and Power Factor Correction

Power Management & Supply



ICE1QS01 Revision History: Current Version: 2004- 04-27		
Previous Version: 2003- 11-28		
Page13 (in previous version)	Page 13 (in current version)	Diagram mains undervoltage lockout curent added
Page 16-18 (in previous version)	Page 16-18 (in current version)	Min max values added, typ. values adapted, according to measuring results.
Page 20 (in previous version)	Page 20 (in current version)	Application circuit changed to new 250 W demo board with PFC current pump.

Edition 2004-04-27

Published by Infineon Technologies AG, St.-Martin-Strasse 53, D-81541 München © Infineon Technologies AG 2004. All Rights Reserved.

Attention please!

The information herein is given to describe certain components and shall not be considered as warranted characteristics.

Terms of delivery and rights to technical change reserved.

We hereby disclaim any and all warranties, including but not limited to warranties of non-infringement, regarding circuits, descriptions and charts stated herein.

Infineon Technologies is an approved CECC manufacturer.

Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office in Germany or our Infineon Technologies Representatives worldwide (see address list).

Warnings

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies Office.

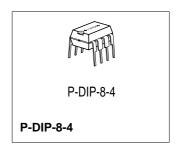
Infineon Technologies Components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons

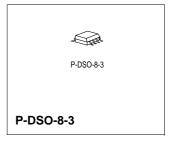


Controller for Switch Mode Power Supplies Supporting Low Power Standby and Power Factor Correction (PFC)

Features

- · Quasiresonant Operation
- Primary and Secondary Regulation
- · Primary Current Simulation
- Standby Input Power < 1 W
- Low Power Consumption
- · Very Low Start-up Current
- · Soft-Start for noiseless Start-up
- Standby Burst Mode with and without Control Signal for lowered Output Voltages
- · Digital Frequency Reduction in small Steps at Decreasing Load
- · Over- and Undervoltage Lockout
- · Switch Off at Mains Undervoltage
- Mains Voltage Dependent Fold Back Point Correction
- · Ringing Suppression Time Controlled from Output Voltage
- · Free usable Fault Comparator





Functional Description

The ICE1QS01 is optimized to control free running flyback converters with and without Power Factor Correction (with PFC Charge Pump).

The switching frequency is reduced in small steps with decreasing load towards a minimum of 20 kHz in standby mode. This function is performed by a digital circuit to avoid any jitter also with periodically pulsed loads. To provide extremely low power consumption at light loads, this device can be switched into Standby Burst Mode. This is also possible without standby control signal (for adapter application).

Additionally, the start up current is very low. To avoid switching stresses of the power devices, the power transistor is always switched on at minimum voltage. The device has several protection functions: V_{CC} overand undervoltage, mains undervoltage and current limiting. Regulation can be done by using the internal error amplifier or an opto coupler feedback. The output driver is ideally suited for driving a power MOSFET.

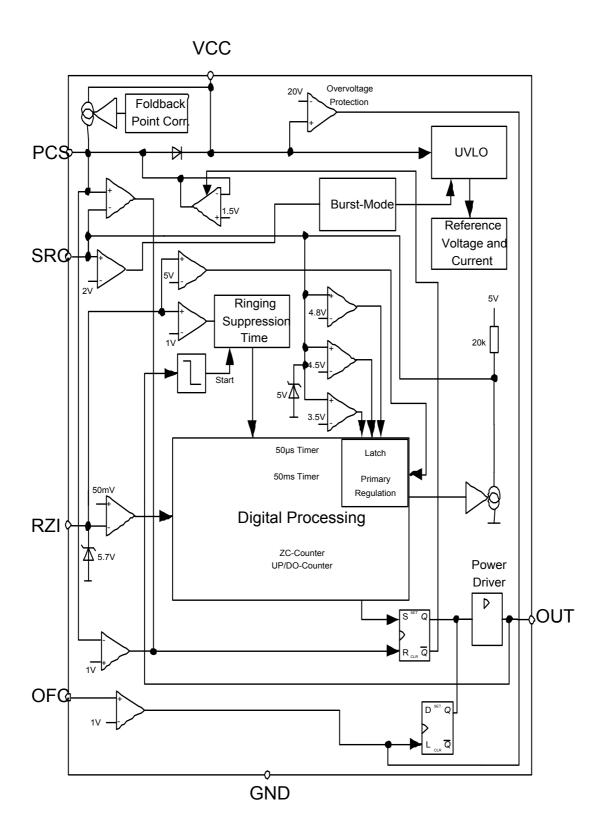
The ICE1QS01 is suited for TV-sets, DVD- sets, SAT- receivers and other consumer applications in the power range from 0 to app. 300 W.

Type	Ordering Code	Package
ICE1QS01	Q67040-S4558	P-DIP-8
ICE1QS01G	Q67040-S4559	P-DSO-8

		a.	
Version 1.4	3		27 Apr 2004



Block Diagram



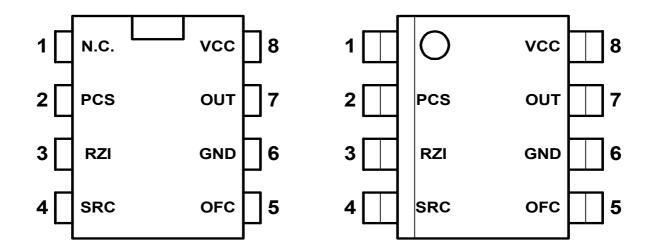
Version 1.4	4	27 Apr 2004



Pinning

Pin	Symbol	Function
1	N.C.	
2	PCS	Primary Current Simulation
3	RZI	Regulation and Zero Crossing Input
4	SRC	Soft-Start and Regulation Capacitor
5	OFC	Overvoltage Fault Comparator
6	GND	Ground
7	OUT	Output
8	VCC	Supply Voltage

Pin Configuration (top view)



Version 1.4	5	27 Apr 2004



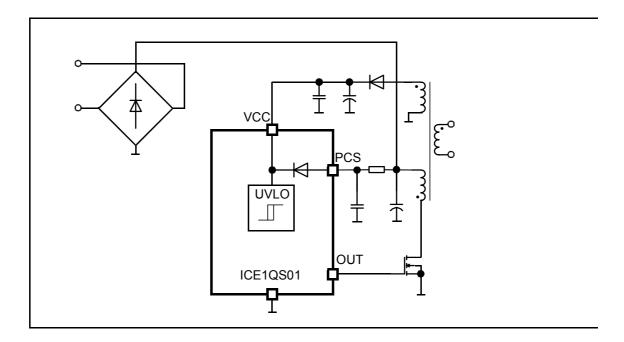
Functional Description

Start up

An internal start up diode is connected between pin PCS and pin V_{CC} . Start up current is provided via this diode if V_{PCS} is higher than $V_{CC} + V_{BE}$ ($V_{BE} = Base-Emitter-Voltage$).

During start up the internal reference of the IC is shut off and current consumption is about 60 μ A. There is only the start up circuitry working which determines the V_{CCon} threshold. Gate driver OUT is switched to low. An active shut down circuitry ensures that OUT is held below the MOS gate threshold when the IC is in start up mode.

Block Diagram: Start Up

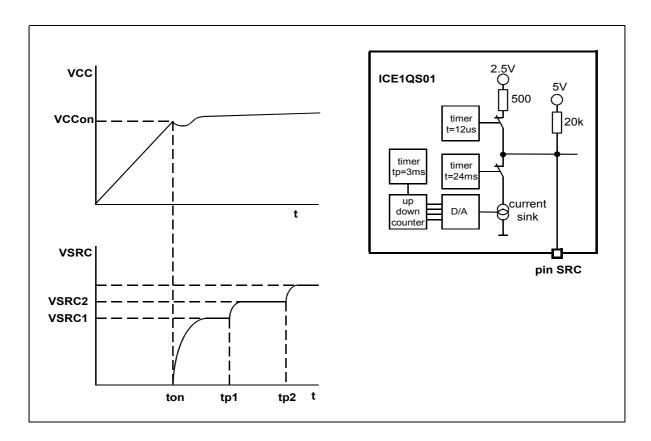




Soft start

The internal reference of the IC is switched on when V_{CC} exceeds the V_{CCon} threshold. The IC begins to work with soft start mode. Soft start is realized with an internal soft start resistor, an internal current sink, a current source and the external feedback capacitor connected at pin SRC. The internal resistor is connected between the internal voltage reference and pin SRC. The current sink is connected between pin SRC and GND. The value of the current is set with a timer. Immediately after the IC is switched on the capacitor C_{SRC} is charged with a current source up to 2.5V. This current source is switched off 12 µsec after beginning of soft start. The current value of the current sink is set with a timer. Every three msec the current of the current sink is reduced and so V_{SRC} can increase stepwise. The soft start is finished 24 msec after the IC is switched on. At the end of the soft start the current sink is switched off.

Figure: Soft Start



PCS (primary current simulation)

A voltage proportional to the current of the power transistor is generated at Pin PCS by the RC-combination R2, C2. The voltage at Pin PCS is forced to 1.5V when the power transistor is switched off and during its switch on time C2 is charged by R2 from the rectified mains. The relation of V_{PCS} and

		a.	
Version 1.4	7		27 Apr 2004



the current in the power transistor (Iprimary) is:

$$VPCS = 1,5V + \frac{Lprimary \times Iprimary}{R2 \times C2}$$

Lprimary: Primary inductance of the transformer

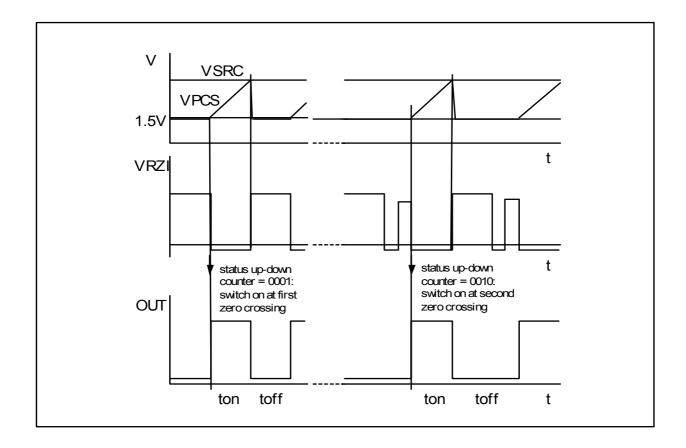
The advantage of primary current simulation is the elimination of the leading edge spike, which is generated when the power transistor is switched on.

RZI (zero crossing input and primary regulation)

Zero current counter

Every time when the falling voltage ramp of V_{RZI} crosses the 50 mV threshold a pulse is sent to the zero-current-counter and increases the counter by one. If zero-current-counter and up-down-counter are equal the gate drive OUT is switched to high. Up-down counter is influenced via SRC voltage as described below. If V_{RZI} is greater than 50 mV gate drive OUT is always switched low.

Figure: Zero Crossing Switching Behaviour



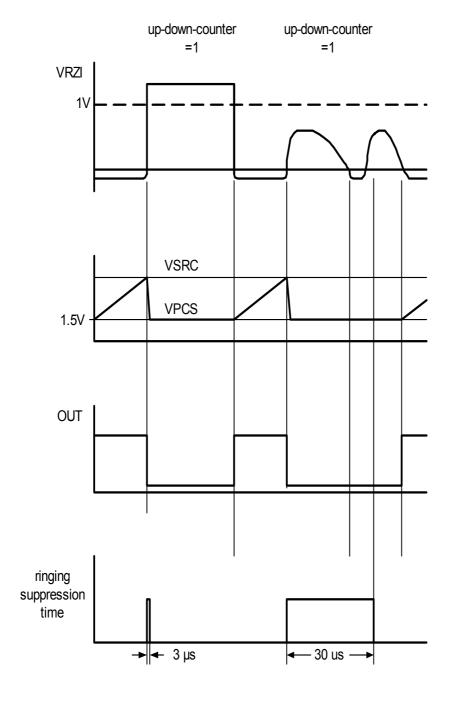
		a.
Version 1.4	8	27 Apr 2004



Ringing suppression

When V_{PCS} reaches the feedback voltage V_{SRC} the gate drive OUT is set to low and the ringing suppression timer is started. This timer ensures that the gate drive cannot be switched on until this ringing suppression time is passed. Duration of ringing suppression time depends on the V_{RZI} voltage. Suppression time is 3 µsec if V_{RZI} > 1V and it is 30 µsec if V_{RZI} < 1V.

Figure: Ringing Suppression

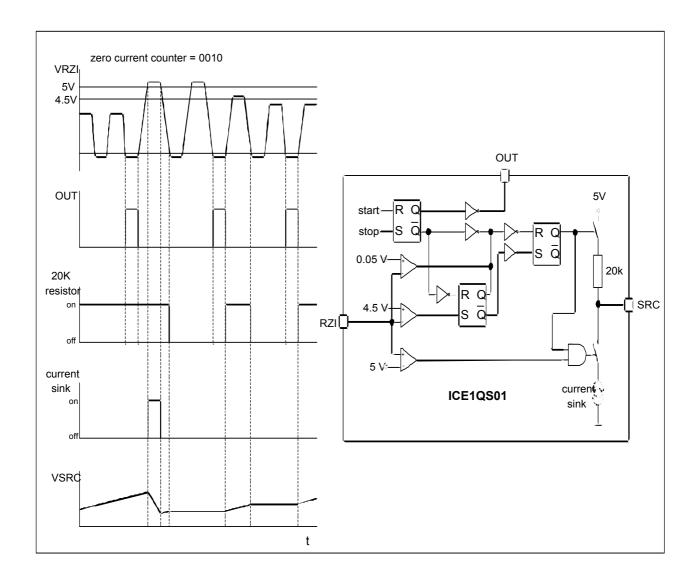




Primary regulation

Primary regulation is achieved by activating the internal current sink. The current sink is connected between pin SRC and ground. If V_{RZI} exceeds the 5V threshold the current sink is switched on. It is switched off when V_{RZI} falls below 5V. The current sink discharges the C_{SRC} capacitor. C_{SRC} is charged via the internal 20k resistor. If V_{RZI} exceeds the 4.4V threshold a flip-flop is set and the resistor is switched off when V_{RZI} falls below 50 mV. The resistor is switched on again with the falling slope of gate drive OUT.

Diagram Primary Regulation





SRC (Regulation and soft start capacitor)

The feedback capacitor is connected to pin SRC. The feedback voltage V_{SRC} has two main functions.

Function I (MOS FET on time): V_{SRC} provides the switch off reference voltage. If V_{PCS} (which contains the primary current information) exceeds the V_{SRC} voltage the external MOS transistor is switched off.

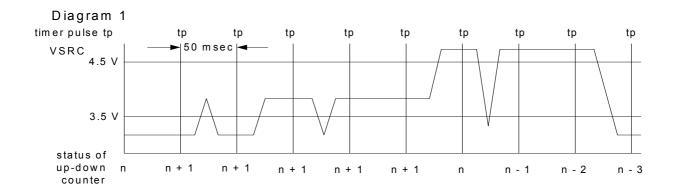
Function II (MOS FET off time for frequency reduction): At low load the frequency is reduced by ignoring zero crossing signals after the transformer demagnetization. V_{SRC} determines the action of the 4-bit up-down-counter which contains the number of zero crossings to be ignored. The content of the up-down-counter is compared with the number of zero-current crossings of V_{RZI} . If the number of zero-current crossings in each period after the transformer demagnetization is equal to the up-down-counter content the MOS is switched on. At low load conditions when V_{SRC} is below 3.5V the counter is increased by one every 50 msec. The result is that the MOS transistor off-time increases and duty cycle decreases. At high load conditions when V_{SRC} is higher than 4.4V the counter content is reduced by one every 50msec. So MOS transistor off-time will be reduced. With this off-time regulation switching jitter can be eliminated.

The up-down-counter is immediately set to 0001 if a load jump occurs and V_{SRC} exceeds 4.8 V. This ensures that full power can be provided instantaneously.

The following table shows the SRC voltage range and the corresponding up-down counter action.

SRC voltage range	up-down-counter action
1: VSRC< 3.5V	count forward
2: 3.5 <vsrc<4.4< td=""><td>stop count</td></vsrc<4.4<>	stop count
3: VSRC>4.4	count backward
4: VSRC> 4.8	set up-down-counter to1

The information provided by V_{SRC} is stored in two independent flip flops. An internal timer creates a trigger pulse with a period of 50 msec. Every time the pulse occures the up-down counter checks the status flip flops and acts depending on the flip flop information. After this pulse the flip flops are reset. So change of voltage range is noticed by the logic only once during the 50 ms period. In the diagram below the behaviour of the up-down counter is depicted in more detail.



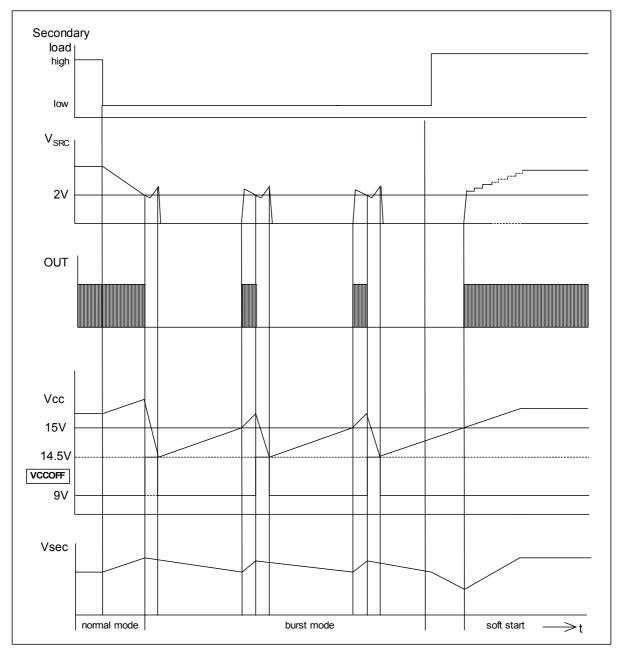
		a.	
Version 1.4	11		27 Apr 2004



Burst mode

12 µsec after beginning of softstart the burst mode comparator is activated. If V_{SRC} falls below 2V after activating the comparator the gate drive OUT is switched to low and the V_{CCoff} threshold is changed to 14.5 V. V_{CC} decreases because gate drive is held low. If V_{CC} reaches the V_{CCoff} threshold the IC is going into start-up mode. At V_{CCon} threshold the IC is switched on again starting with soft start modus. V_{CCoff} threshold is set to the normal 9V.

Figure: Burst Mode



		a.	
Version 1.4	12		27 Apr 2004



Restart timer

If voltage V_{RZI} is lower than 50 mV and gate drive OUT is low an internally created restart pulse will switch gate drive OUT high every 50 μ s and the minimum switching frequency is about 20 kHz.

Restart pulse is inhibited if V_{RZI} is higher than 50 mV. So the MOS transistor cannot be switched on until the transformer is discharged.

VCC overvoltage protection

If V_{CC} exceeds the V_{CCD} threshold a latch is set and the gate is disabled. Reset of latch occurs when V_{CC} is falling below V_{CCon} - V_{CCBHY} .

Overvoltage fault comparator (OFC)

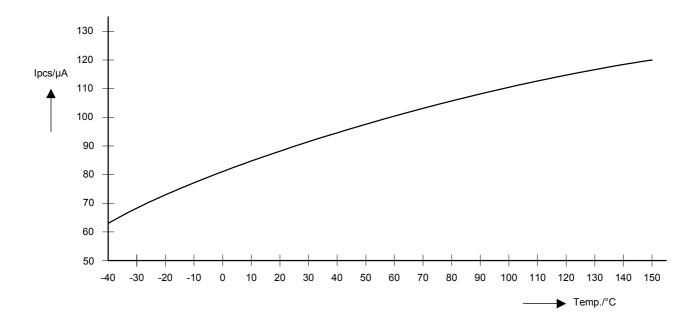
With an external sense resistor connected to pin OFC primary current can be sensed directly. If the sensed current exceeds the internal V_{OFC} threshold a latch is set and gate is disabled. Reset of latch occurs when V_{CC} is falling below $V_{CCon^-}V_{CCBHY}$.

Notice: If this comparator is not used pin OFC has to be connected to ground.

Mains undervoltage

Power supplies must be shut down when mains voltage is below a certain limit to avoid too long ontime of MOS-FET switch, which would lead to a switching frequency in audible spheres. Mains undervoltage is sensed during the off-time of the MOS-FET switch. If the current flowing into pin PCS is smaller than 100 uA, then the output is latched and cannot be switched to high state.

Diagram Mains Undervoltage Lockout Current



Version 1.4	13	27 Apr 200)4
-------------	----	------------	----



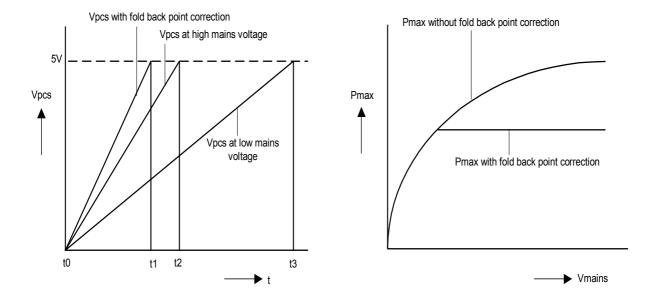
Fold back point correction

With increasing mains voltage the switch on time becomes shorter and so the frequency becomes higher. With higher frequency also the maximal possible output power becomes higher. With higher power the danger in case of failure increases.

To avoid this, the foldback point correction circuit senses main voltage to reduce the on-time of the switch. Mains voltage is sensed at the supply coil of V_{CC} voltage via a resistor connected to pin RZI. During on-time of the MOS-FET switch current is pulled out from pin RZI. When this current is higher than 500 μ A, one fifth of the current higher than this threshold is driven into pin PCS to increase the voltage slope charging the capacitor connected to this pin.

$$IPCSFO = \frac{IRZI - 0.5mA}{5}, (IRZI > 500uA)$$

Figure: Fold Back Point Correction



Version 1.4	14	27 Apr 2004
-------------	----	-------------



Absolute Maximum Ratings

Parameter	Symbol	Min	Max	Unit	Remark
Charge Current into Pin2	I _{PCS}		500	uA	During start up
Voltage at Pin 2	V _{PCS}	-0.3	21	V	
Current into Pin 3	I _{RZI} I _{RZI}	-10	10	mA mA	V _{RZI} >V _{RZICH} V _{RZI} <v<sub>RZICL</v<sub>
Voltage at Pin 4	V _{SRC}	-0.3	V _{SRCCL}	V	I _{SRC} =100 μA
Voltage at Pin 5	V _{OFC}	-0.3	6	V	
Current into Pin 7	l _{OUT}	-500	500	mA	t<1ms
Voltage at Pin 8	V _{CC}	-0.3	21	V	
ESD Protection			4000	V	MIL STD 883C method 3015.6, 100pF,1500Ω
Storage Temperature	T _{stg}	-50	150	°C	
Operating Junction Temperature	T _J	-25	150	°C	
Thermal Resistance Junction-Ambient	R _{thJA}		100	K/W	P-DIP-8



Characteristics (Unless otherwise stated, -25°C<Tj <150 °C, VCC = 16V)

Parameter	Symbol	min.	typ.	max.	Unit	Test Condition
VCC start-up circuit		•	•			
Start-up supply current	I _{CCL}		60	100	μA	V _{CC} =V _{CCon} -0.5V
Operating supply current	I _{CCH}	8	11	12.5	mA	Output low
V _{CC} Turn-On threshold	V _{CC ON}	14.1	15	15.5	V	
V _{CC} Turn-Off threshold	V _{CC OFF}	8.5	9	9.5	V	
V _{CC} Hysteresis	V _{CCHY}	5.4	6	6.5	V	
V _{CC} Burst Hysteresis	V _{CCBHY}	0.2	0.4	0.6	V	
V _{CC} Overvoltage	V _{CCD}	19	20	21	V	
SRC soft start mode						
Start Voltage	V _{SRC1}	2.40	2.65	2.85	V	I _{optocoupler} =0 μA
Digital voltage step	V _{SRCST}		360		mV	I _{optocoupler} =0 μA
Step pulse rate	t _{SRCSTR}		3		ms	
Soft start time	t _{ST}	19	24	32	ms	
Current source rise time	t _{STRT}		14		μs	V _{SRC} =0.2V to 2.0V C _{SRC} =10nF
Current source on time	t _{STOT}		12		μs	
SRC normal mode		•		•	•	
Source resistor	R _{SRC}	17	21	28	kOhm	
Clamping threshold voltage	V _{SRCCL}	4.95	5.1	5.25	V	V _{PCS} =V _{SRC} , OUT switches to Low, I _{SRC} =100μA
Reset counter to one	V _{SRCR}	4.75	4.9	5.05	V	
Distance clamping to reset	V _{SRCH}	150	200	250	mV	
Threshold downward count	V _{SRCD}	4.3	4.5	4.7	V	
Threshold upward count	V _{SRCSU}	3.4	3.5	3.7	V	
Burst mode latch threshold voltage	V _{SRCB}	1.9	2.05	2.2	V	V _{SRC} <v<sub>SRCB: OUT=Low</v<sub>
Counter time 1)	tCOUNT		50		msec	
Sink current prim reg mode	I _{SRCS}	400	500	550	μΑ	V _{RZI} > 5V
1) The parameter is not subj	ect to produc	ction test	- verified	by desig	n/charact	terization

Version 1.4	16	27 Apr 2004



Parameter	Symbol	min.	typ.	max.	Unit	Test Condition
RZI (regulation and ze	ro crossir	ng inpu	it)	•	1	
Zero crossing threshold voltage	V _{RZIT1}	25	50	80	mV	V _{RZI} <v<sub>RZIT1: Out=High</v<sub>
Time delay switch on	t _{don}	350	440	550	nsec	
Leakage current	I _{RZIB}	-1	25	110	μΑ	V _{RZI} =5V
Clamping voltage low state	V _{RZICL}	-0.5	-0.3	-0.2	V	I _{RZI} = -1mA
Clamping voltage high state	V _{RZICH}	5.5	6.0	6.4	V	I _{RZI} = 5mA
Primary regulation threshold for discharge current	V _{RZIDC}	4.95	5.1	5.25	V	
Primary regulation threshold for charge current	V _{RZICC}	4.2	4.4	4.65	V	
Ringing suppression threshold voltage	V _{RZIT2}	0.9	1.0	1.1	V	
Ringing suppression time	t _{RZIPS}	1.5 20	2.5 29	3.2 37	µsec µsec	V _{RZI} > V _{RZIT2} V _{RZI} < V _{RZIT2}
Foldback point correction current threshold	I _{PCSF}	250	400	600	μΑ	-25°C <tj<120°c< td=""></tj<120°c<>
PCS (primary current	simulation	1)			U.	
Gate enable threshold voltage	V _{PCSE}	0.9	1.0	1.1	V	V _{PCS} <v<sub>PCSE: Out=Low</v<sub>
Basic voltage	V _{PCSB}	1.45	1.55	1.65	V	gate low
Shut down delay	t _{PCS}		150	230	nsec	
Mains undervoltage lock- out current 2)	I _{PCS}	40	100	160	μA	
Voltage drop startup diode	V _{PCSD}		0.85		V	I _{PCS} =300μA
Discharge current	I _{PCSD}	1.6	2.6	3.6	mA	V _{PCS} =3V
OFC (overcurrent faul	t compara	tor)				
Bias Current	I _{OFCB}	-1			μA	
Gate drive disabled threshold voltage	V _{OFC}	0.93	1.0	1.05	V	
Shut Down Delay	t _{OFC}		180	240	ns	
See diagram mains undervolt. lockout current						

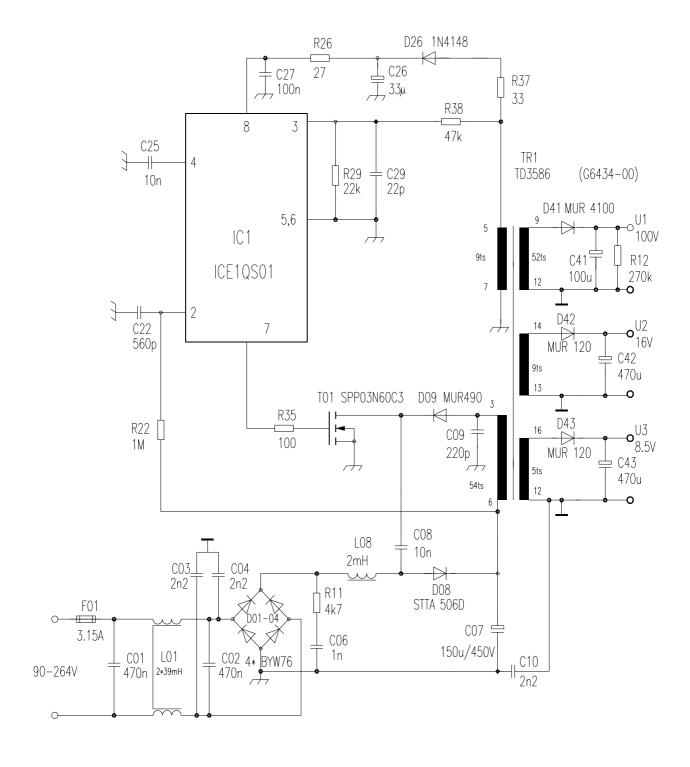
	4		
Version 1.4		17	27 Apr 2004



Parameter	Symbol	min.	typ.	max.	Unit	Test Condition
Restart Timer						
Restart time	t _{RES}	33	42	55	μs	V _{RZI} <25mV
Gate Drive						
Output voltage low			0.7 0.8	1.1 1.4	V V	I _{OUT} =20mA I _{OUT} =200mA
Output voltage high		9.5 9.5	10.6 10.5	11.0 11.0	V V	I _{OUT} =-20mA I _{OUT} =-180mA
Output voltage active shut down			1.0	1.35	V	V _{CC} =7V I _{OUT} =20mA
Rise time			40	100	ns	C _{OUT} =1nF
Fall time			60	120	ns	C _{OUT} =1nF



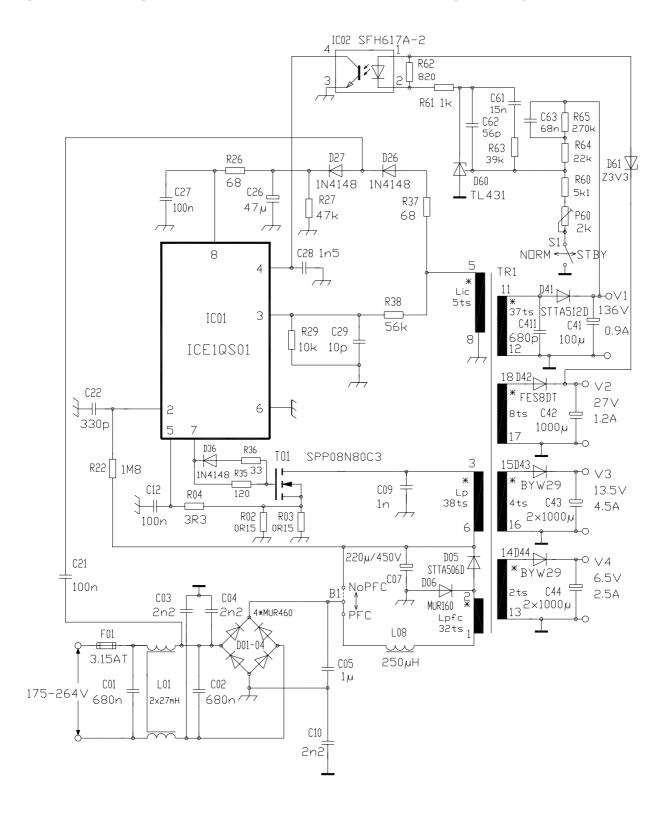
Figure: Circuit Diagram for Standard Application with PFC



Version 1.4	27 Apr 2004
-------------	-------------



Figure: Circuit Diagram for Application with PFC and Low Voltage Standby Mode

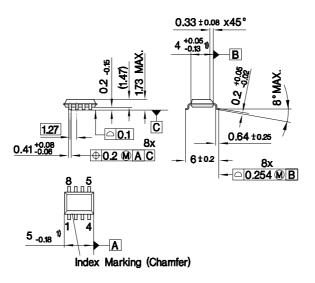


	4		
Version 1.4		20	27 Apr 2004



Plastic Package, P-DSO-8-3

(Plastic Dual Small Outline Package)

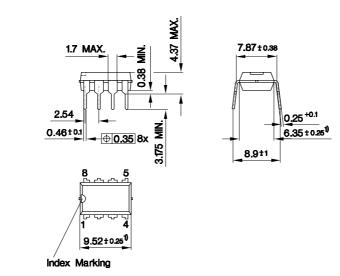


1) Does not include plastic or metal protrusion of 0.15 max. per side

1000

Plastic Package, P-DIP-8-4

(Plastic Dual In-line Package)



1) Does not include plastic or metal protrusion of 0.25 max. per side

5005000

Sorts of Packing

Package outlines for tubes, trays etc. are contained in our Data Book "Package Information".

SMD = Surface Mounted Device

Dimensions in mm

Version 1.4	21	27 Apr 2004